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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/785166
		Filing Date	2-23-04
		First Named Inventor	Farid Nemati
		Art Unit	2813
		Examiner Name	VESPERMAN
Sheet 1	of 3	Attorney Docket Number	C033-D-1

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
WAV		US- 6,229,161	5-8-2001	Nemati et al.	---
WAV		US- 6,104,045	8-15-2000	Forbes et al.	---
WAV		US- 4,797,373	1-10-1989	Malhi et al.	---
WAV		US- 6,225,165	5-1-2001	Noble, Jr. et al.	---
WAV		US- 5,528,062	6-18-1996	Hsieh et al.	---
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WAV		US- 6,084,274	7-2000	Mukai et al.	---
WAV		US- 5,600,160	2-1997	Hvistendahl	---
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WAV		US- 6,583,452	6-2003	Cho et al.	---
WAV		US- 4,395,723	7-1983	Harari	---
WAV		US- 2002/0190265 A1	12-2002	Hsu et al.	---
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FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)			
WAV		Japan 3-16089	1-1991	Sato et al.	

Examiner Signature	William Verge	Date Considered	10/19/04
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Sheet 2	of 3	Attorney Docket Number	C033-D-1

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
we		K. DeMeyer, S. Kubicek and H. van Meer, Raised Source/Drains with Disposable Spacers for sub 100 nm CMOS Technologies, Extended Abstracts of International Workshop on Junction Technology 2001.	
we		Mark Rodder and D. Yeakley, Raised Source/Drain MOSFET with Dual Sidewall Spacers, IEEE Electron Device Letters, Vol. 12, No. 3, March 1991	
we		Yang-Kyu Choi, Daewon Ha, Tsu-Jae King and Chenming Hu, Nanoscale Ultrathin PMOSFETs with Raised Selective Germanium Source/Drain, IEEE Electron Device Letters, Vol. 22, No. 9, September 2001.	
we		N. Lindert, Y. K. Choi, L. Chang, E. Anderson, W. C. Lee, T. J. King, J. Bokor, and C. Hu, Quasi-Planar FinFETs with Selectively Grown Germanium Raised Source/Drain, 2001 IEEE International SOI Conference, 10/2001	
we		T. Ohguro, H. Naruse, H. Sugaya, S. Nakamura, E. Morifuji, H. Kimijima, T. Yoshitomi, T. Morimoto, H.S. Momose, Y. Katsumata, and H. Iwai, High Performance RF Characteristics of Raised Gate/Source/Drain CMOS with Co Salicide, 1998 Symposium on VLSI Technology Digest of Technical Papers	
we		Hsiang-Jen Huang, Kun-Ming Chen, Tiao-Yuan Huang, Tien-Sheng Chao, Guo-Wei Huang, Chao-Hsin Chien, and Chun-Yen Chang, Improved Low Temperature Characteristics of P-Channel MOSFETs with Si1-xGex Raised Source and Drain, IEEE Transactions on Electron Devices, Vol. 48, No. 8, August 2001	
we		Nemati, Farid, and Plummer, James, D., "A Novel High Density, Low voltage SRAM Cell with a Vertical NDR Device," VLSI Technology Technical Digest, June 1998	
we		Stanley Wolf Ph.D. and Richard N. Tauber Ph.D., Silicon Processing for the VLSI Era, Vol. 1, 1986, page 285-286	
we		Nemati, Farid, and Plummer, James, D., "A Novel Thyristor-Based SRAM Cell (T-RAM) for High Speed, Low Voltage, Giga-Scale Memories," International Electron Device Meeting Technical Digest, 1999	

Examiner Signature	William Vegelin	Date Considered	11/1/04
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wa		NN80081017, Single Thyristor Static Memory and its Fabrication, 8/1980, IBM, Technical Disclosure Bulletin, Vol. 23, Issue 3, pp. 1017-25	
wa		Zeng et al., Effect of Carrier Lifetimes on Forward Characteristics of MOS-Controlled Thyristors, 6/1995, IEE, IEE Proc.-Circuits Devices Syst., Vol. 142, No. 3, pp. 205-07	
wa		Kim et al., Realization of a Fast Switching Thyristor by Local Carrier Lifetime Control, 5/2002, IEEE, Proc. 23rd International Conference on Microelectronics, Vol. 1, pp. 193-96	

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